DATA SHEET

NEC

MOS FIELD EFFECT TRANSISTOR

2SK3113B

SWITCHING
N-CHANNEL POWER MOS FET

DESCRIPTION

The 2SK3113B is N-channel MOS FET device that features a low gate charge and excellent switching characteristics, and designed for high voltage applications such as switching power supply, AC adapter.

FEATURES

- Low on-state resistance
  $R_{DS(on)}$ = 4.4 Ω MAX. (V_{GS} = 10 V, I_D = 1.0 A)
- Low gate charge
  Q_G = 7.9 nC TYP. (V_{DD} = 450 V, V_{GS} = 10 V, I_D = 2.0 A)
- Gate voltage rating : ±30 V
- Avalanche capability ratings

<R> ORDERING INFORMATION

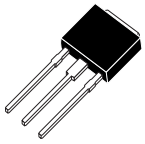
PART NUMBER	LEAD PLATING	PACKING	PACKAGE
2SK3113B-S15-AY Note	Pure Sn (Tin)	Tube 70 p/tube	TO-251 (MP-3-a) typ. 0.39 g
2SK3113B(1)-S27-AY Note		Tube 75 p/tube	TO-251 (MP-3-b) typ. 0.34 g
2SK3113B-ZK-E1-AY Note		Tape 2500 p/reel	TO-252 (MP-3ZK) typ. 0.27 g
2SK3113B-ZK-E2-AY Note			

Note Pb-free (This product does not contain Pb in external electrode.)

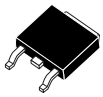
ABSOLUTE MAXIMUM RATINGS (T_A = 25°C)

Drain to Source Voltage (V_{GS} = 0 V)	V_{DSS}	600	V
Gate to Source Voltage (V_{DS} = 0 V)	V_{GSS}	±30	V
Drain Current (DC) (T_C = 25°C)	$I_{D(DC)}$	±2.0	A
Drain Current (pulse) Note1	$I_{D(pulse)}$	±8.0	A
Total Power Dissipation (T_C = 25°C)	P_{T1}	20	W
Total Power Dissipation (T_A = 25°C) Note2	P_{T2}	1.0	W
Channel Temperature	T_{ch}	150	°C
Storage Temperature	T_{stg}	–55 to +150	°C
Single Avalanche Current Note3	I_{AS}	2.0	A
Single Avalanche Energy Note3	E_{AS}	2.7	mJ

(TO-251)



(TO-252)



Notes 1. PW ≤ 10 μs, Duty Cycle ≤ 1%

2. Mounted on glass epoxy board of 40 mm × 40 mm × 1.6 mm

3. Starting T_{ch} = 25°C, V_{DD} = 150 V, R_G = 25 Ω, V_{GS} = 20 → 0 V

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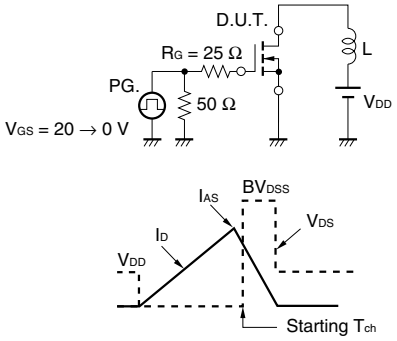
The mark <R> shows major revised points.
The revised points can be easily searched by copying an "<R>" in the PDF file and specifying it in the "Find what:" field.

ELECTRICAL CHARACTERISTICS (T_A = 25°C)

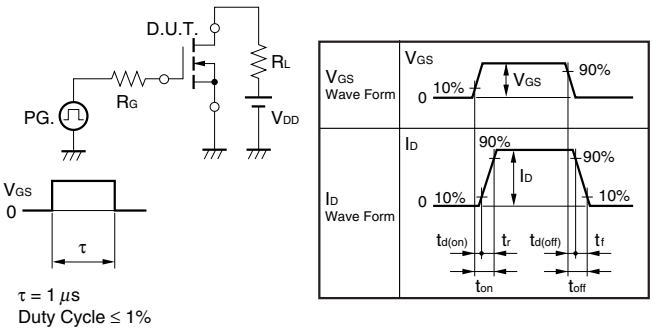
CHARACTERISTICS	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 600 V, V_{GS} = 0 V			100	μA
Gate Leakage Current	I_{GSS}	V_{GS} = ±30 V, V_{DS} = 0 V			±10	μA
Gate Cut-off Voltage	$V_{GS(off)}$	V_{DS} = 10 V, I_D = 1 mA	2.5		3.5	V
Forward Transfer Admittance Note	$\|y_{fs}\|$	V_{DS} = 10 V, I_D = 1.0 A	0.5	0.9		S
Drain to Source On-state Resistance Note	$R_{DS(on)}$	V_{GS} = 10 V, I_D = 1.0 A		3.2	4.4	Ω
Input Capacitance	C_{iss}	V_{DS} = 10 V		290		pF
Output Capacitance	C_{oss}	V_{GS} = 0 V		75		pF
Reverse Transfer Capacitance	C_{rss}	f = 1 MHz		7		pF
Turn-on Delay Time	$t_{d(on)}$	V_{DD} = 150 V, I_D = 1.0 A		10.5		ns
Rise Time	t_r	V_{GS} = 10 V		4.8		ns
Turn-off Delay Time	$t_{d(off)}$	R_G = 10 Ω		15.8		ns
Fall Time	t_f	R_L = 10 Ω		10.5		ns
Total Gate Charge	Q_G	V_{DD} = 450 V		7.9		nC
Gate to Source Charge	Q_{GS}	V_{GS} = 10 V		2.7		nC
Gate to Drain Charge	Q_{GD}	I_D = 2.0 A		3.2		nC
Body Diode Forward Voltage Note	$V_{F(S-D)}$	I_F = 2.0 A, V_{GS} = 0 V		0.8		V
Reverse Recovery Time	t_{rr}	I_F = 2.0 A, V_{GS} = 0 V		190		ns
Reverse Recovery Charge	Q_{rr}	di/dt = 50 A/μs		500		nC

Note Pulsed

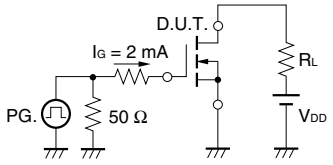
TEST CIRCUIT 1 AVALANCHE CAPABILITY



TEST CIRCUIT 2 SWITCHING TIME

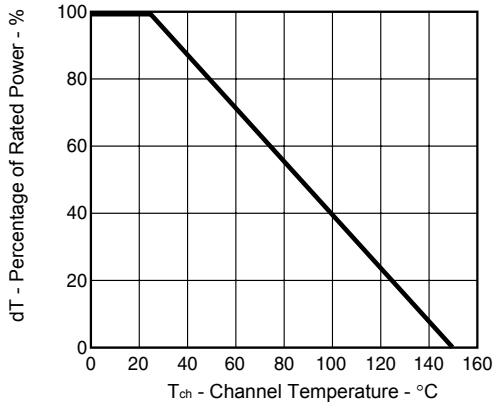


TEST CIRCUIT 3 GATE CHARGE

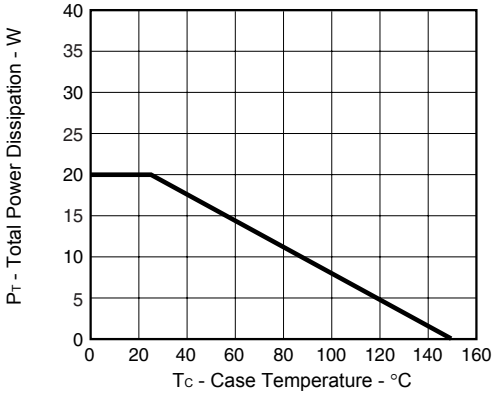


TYPICAL CHARACTERISTICS (T_A = 25°C)

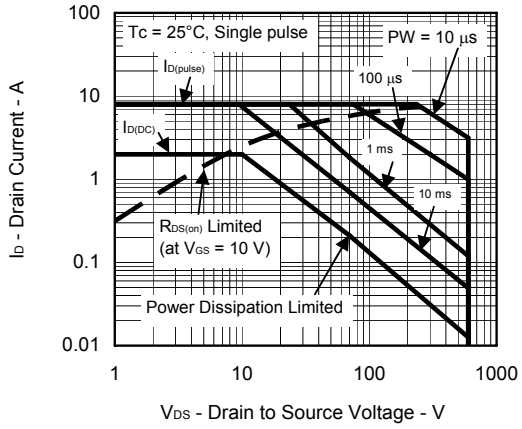
DERATING FACTOR OF FORWARD BIAS SAFE OPERATING AREA



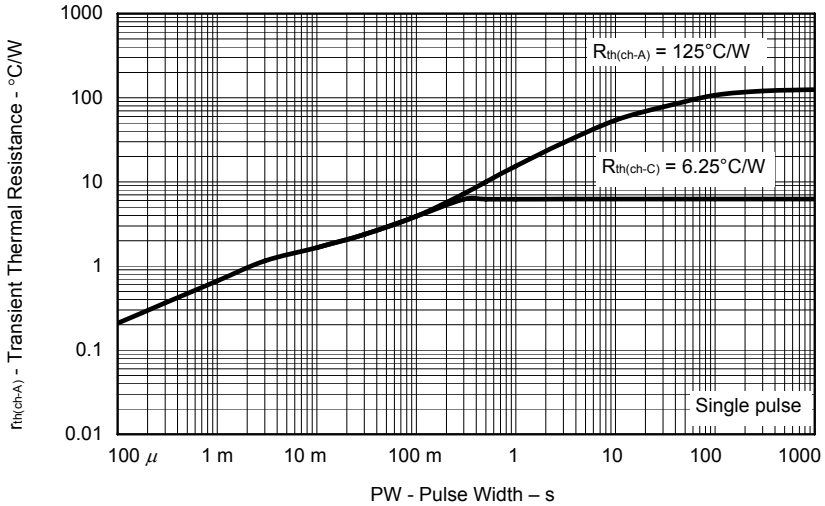
TOTAL POWER DISSIPATION vs. CASE TEMPERATURE



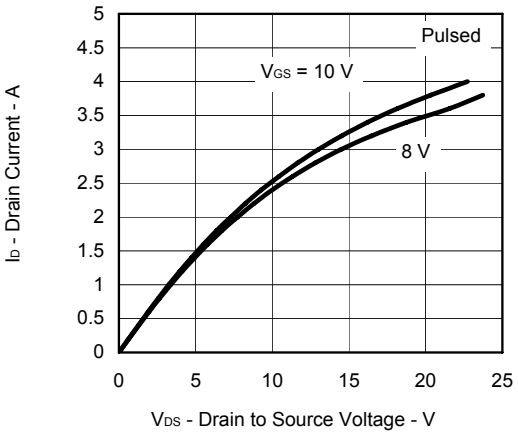
FORWARD BIAS SAFE OPERATING AREA



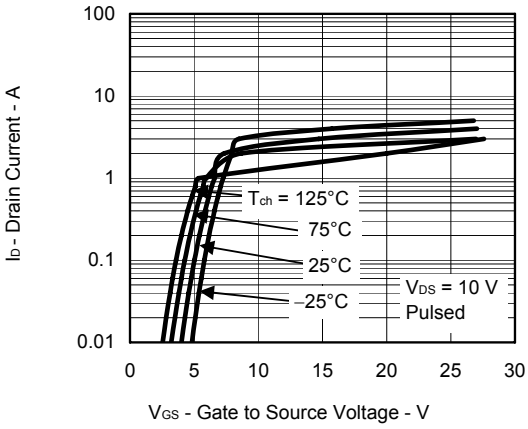
TRANSIENT THERMAL RESISTANCE vs. PULSE WIDTH



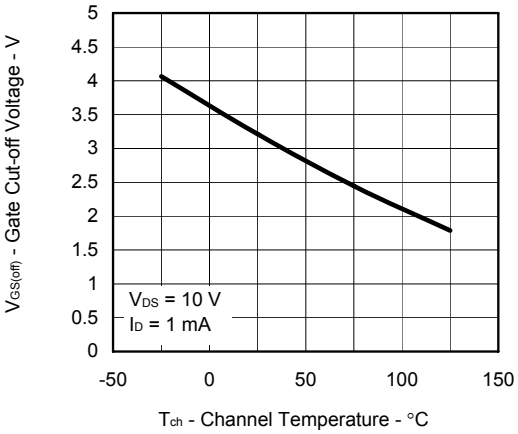
DRAIN CURRENT vs.
DRAIN TO SOURCE VOLTAGE



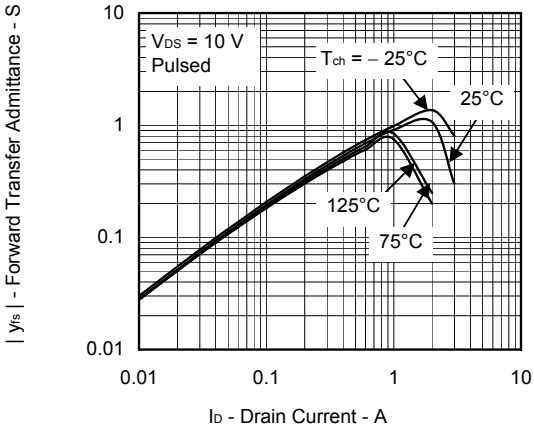
FORWARD TRANSFER CHARACTERISTICS



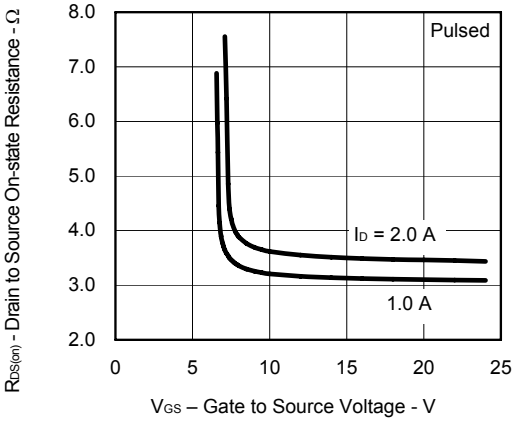
GATE CUT-OFF VOLTAGE vs.
CHANNEL TEMPERATURE



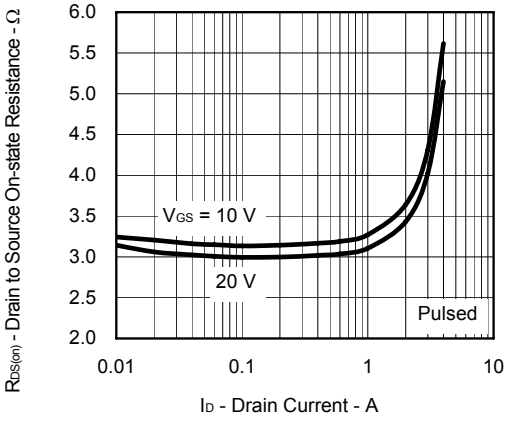
FORWARD TRANSFER ADMITTANCE vs.
DRAIN CURRENT



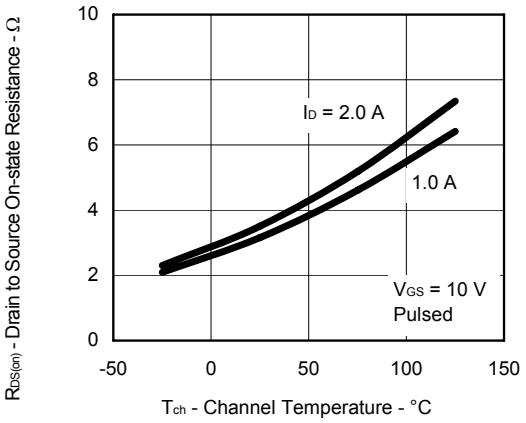
DRAIN TO SOURCE ON-STATE RESISTANCE vs.
GATE TO SOURCE VOLTAGE



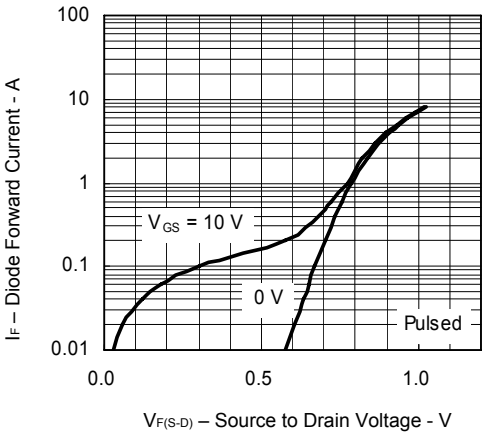
DRAIN TO SOURCE ON-STATE
RESISTANCE vs. DRAIN CURRENT



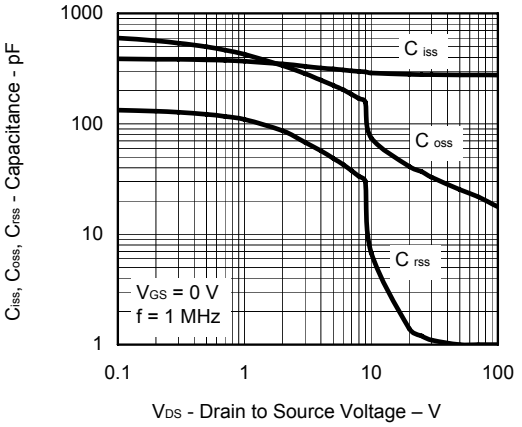
DRAIN TO SOURCE ON-STATE RESISTANCE vs. CHANNEL TEMPERATURE



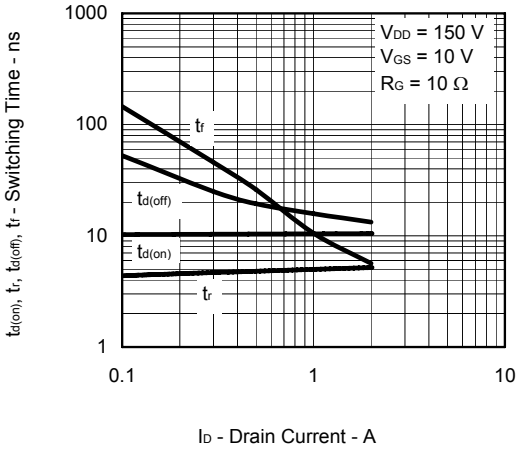
SOURCE TO DRAIN DIODE FORWARD VOLTAGE



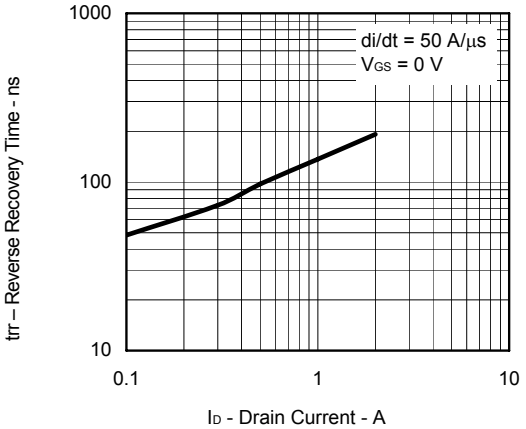
CAPACITANCE vs. DRAIN TO SOURCE VOLTAGE



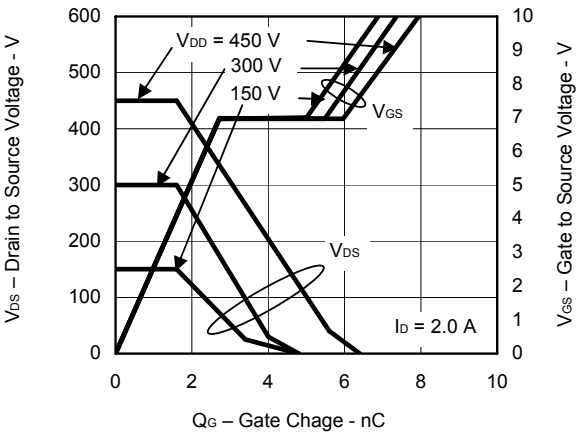
SWITCHING CHARACTERISTICS



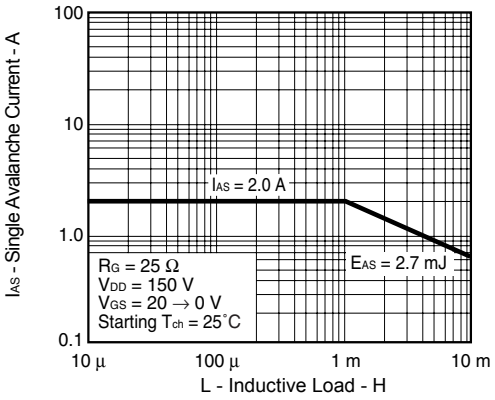
REVWESE RECOVERY TIME vs. DRAIN CURRENT



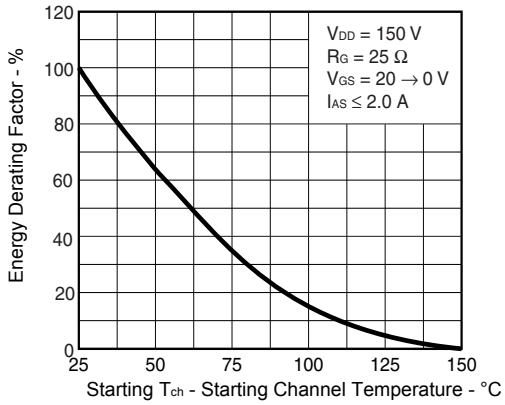
DYNAMIC INPUT/OUTPUT CHARACTERISTICS



SINGLE AVALANCHE CURRENT vs.
INDUCTIVE LOAD

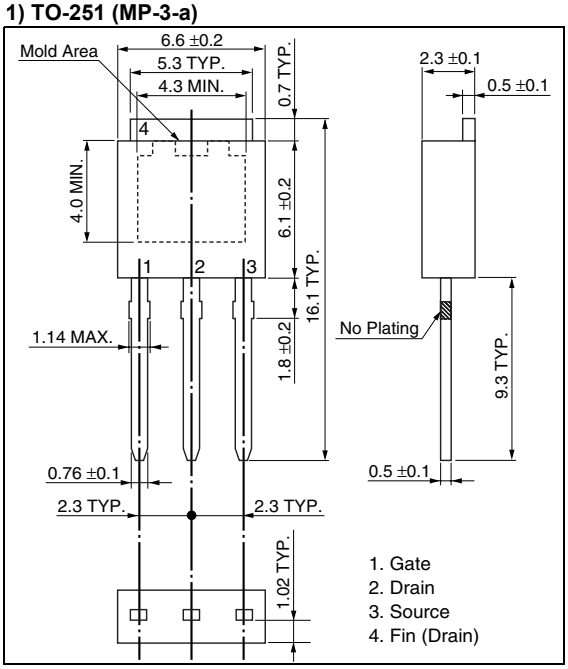


SINGLE AVALANCHE ENERGY
DERATING FACTOR

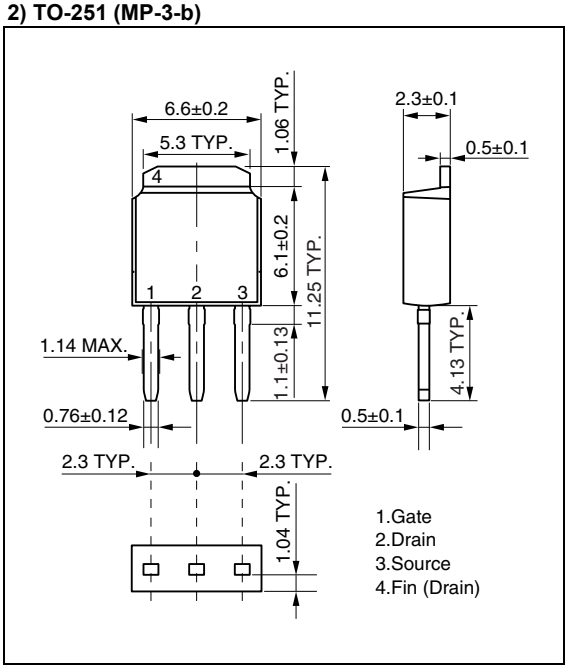


<R> **PACKAGE DRAWINGS (Unit: mm)**

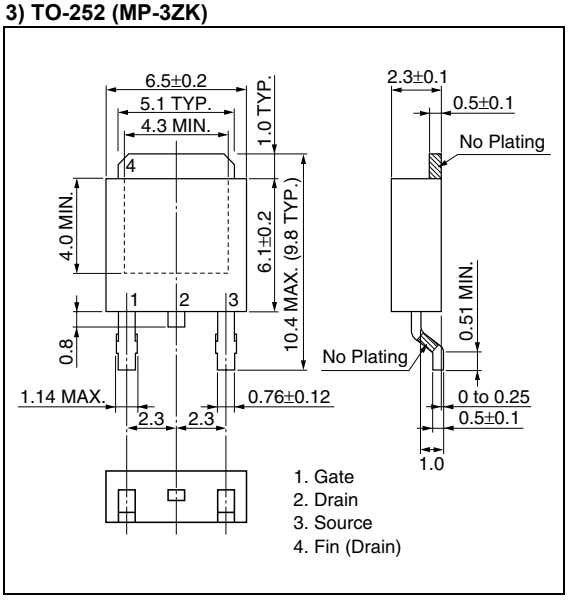
1) TO-251 (MP-3-a)



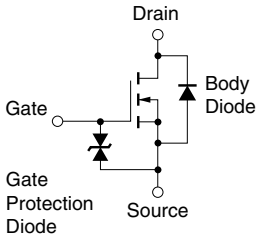
2) TO-251 (MP-3-b)



3) TO-252 (MP-3ZK)



EQUIVALENT CIRCUIT



Remark The diode connected between the gate and source of the transistor serves as a protector against ESD. When this device actually used, an additional protection circuit is externally required if a voltage exceeding the rated voltage may be applied to this device.

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